

S1F78B17 Series Technical Manual

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1. DESCRIPTION

The S1F78B17 is a positive-voltage CMOS regulator IC. This IC provides the low output noise, high-speed load transient response, high-load stability, and high accuracy mechanisms.

The output voltage is fixed in the IC, and its allowance is between 1.5 to 4.0 V based on the laser trimming technique.

This IC consists of the reference voltage supply, output voltage setting resistor, overcurrent protection circuit, output voltage drop correction circuit, phase compensation circuit, chip enable circuit, pulse response circuit, and other components.

There are two kinds of packages provided: SOT23 and WCSP (size: 0.92 [mm] × 0.92 [mm]).

1.1 Features

- | | |
|--|--|
| ● Low consumption current | At no-load operation [Typ.] 30μA, In standby [Max.] 0.1μA |
| ● Output voltage | DC 1.5V to 4.0V (Can be set in 0.1V steps.) |
| ● Output current | 150mA ($V_{DD}=V_{OUT(S)}+1.0V$) |
| ● Input-output potential difference | [Typ.] 0.30V ($V_{OUT(S)}=3.3V$, $V_{DD}=4.3V$, $I_{OUT}=150mA$) |
| ● Output voltage accuracy | ±2.0% |
| ● Output voltage temperature coefficient | [Typ.] ±100ppm/°C |
| ● Ripple rejection | [Typ.] 60dB (f=1kHz) |
| ● Overcurrent detection current | [Typ.] 350mA |
| ● Short-circuit holding current | [Typ.] 50mA |
| ● Range of ceramic capacitor | $C_{in}=1.0\mu F$, $C_{out}=0.47\mu F$ |

1.2 Package

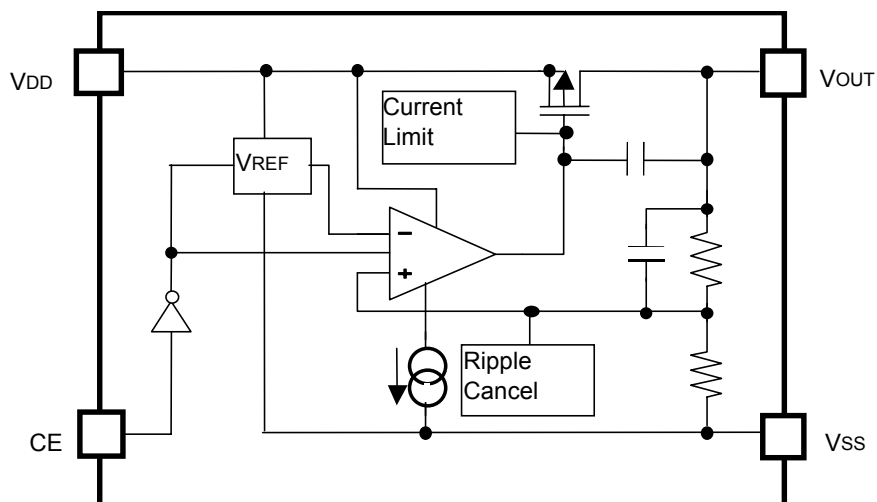
SOT23	5PIN
WCSP	4PIN

1.3 Application

- Mobile communication equipment (Mobile-phone, cordless phone, radio communication equipment)
- Camera, video equipment
- Mobile AV equipment
- Portable game device
- Home appliance
- Battery equipment

2. BLOCK DIAGRAM

2. BLOCK DIAGRAM



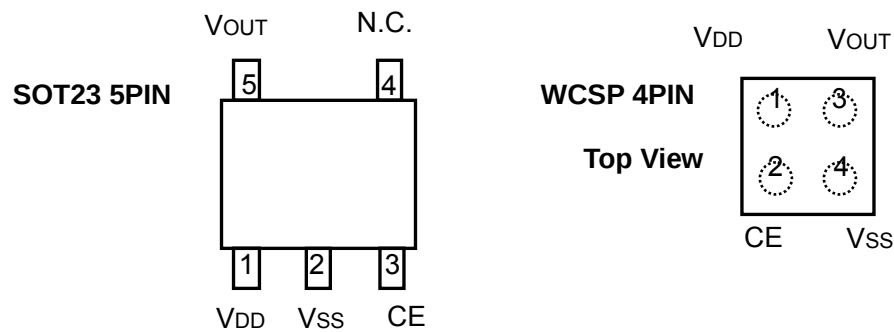
2.1 Selection guide

S1F78B17 * * * 0 0 * *

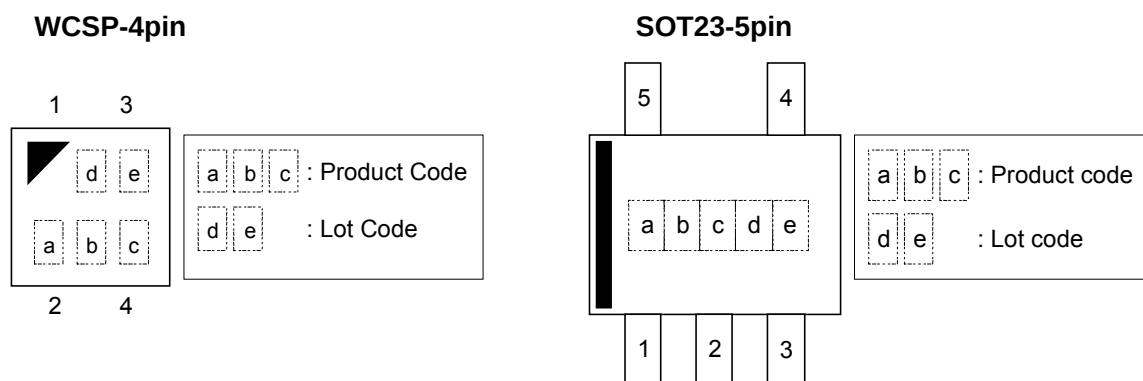
 a b c d e

a	Package type Y SOT23-5pin B WCSP-4pin
b	Indicates the output voltage with a 2-digit value by decoupling the value.
c	Fixed to "0" in this IC.
d	Fixed to "0" in this IC.
e	Taping form (See the packing specifications.) 0R TR type

2.2 Pin assignment

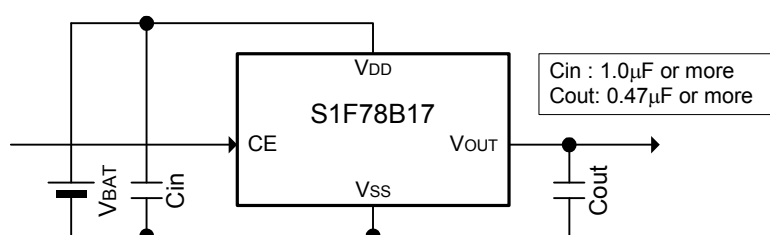


2.3 Marking



VOUT option	a	b	c	VOUT option	a	b	c	VOUT option	a	b	c
—	—	—	—	2.6V	C	0	G	—	—	—	—
—	—	—	—	2.7V	C	0	H	—	—	—	—
—	—	—	—	2.8V	C	0	J	—	—	—	—
—	—	—	—	2.9V	C	0	K	—	—	—	—
1.5V	C	0	5	3.0V	C	P	0	—	—	—	—
1.6V	C	0	6	3.1V	C	P	1	—	—	—	—
1.7V	C	0	7	3.2V	C	P	2	—	—	—	—
1.8V	C	0	8	3.3V	C	P	3	—	—	—	—
1.9V	C	0	9	3.4V	C	P	4	—	—	—	—
2.0V	C	0	A	3.5V	C	P	5	—	—	—	—
2.1V	C	0	B	3.6V	C	P	6	—	—	—	—
2.2V	C	0	C	3.7V	C	P	7	—	—	—	—
2.3V	C	0	D	3.8V	C	P	8	—	—	—	—
2.4V	C	0	E	3.9V	C	P	9	—	—	—	—
2.5V	C	0	F	4.0V	C	P	A	—	—	—	—

2.4 Recommended circuit diagram



3. PIN DESCRIPTION

3. PIN DESCRIPTION

SOT23-5pin

Pin No.	Pin Name	Function
1	VDD	Power input pin
2	VSS	GND pin
3	CE	Chip enable pin (H:Enable / L:Disable)
4	N.C.	No connection
5	VOUT	Voltage output pin

WCSP-4pin

Pin No.	Pin Name	Function
1	VDD	Power input pin
2	CE	Chip enable pin (H:Enable / L:Disable)
3	VOUT	Voltage output pin
4	VSS	GND pin

4. ABSOLUTE MAXIMUM RATINGS

(Unless otherwise specified: Ta=25°C)

Item	Symbol	Rating		Unit
Power voltage	VDD	VSS-0.3 to VSS+7.0		V
Output voltage	VOUT	VSS-0.3 to VDD+0.3		V
Output current	IOUT	150		mA
CE input voltage	VCE	VSS-0.3 to VDD+0.3		V
Allowable dissipation	PD	SOT23WCSP	300T.B.D.	mW
Operating ambient temperature	Topr	-40 to +85		°C
Storage ambient temperature	Tstg	-55 to +125		°C

(Note) To stabilize the IC, insert the decoupling capacitor between VDD and VSS.

- *1) Installation conditions at measurement of SOT23 allowable dissipation (Board specifications)
Glass epoxy, 40 × 40 × 1.6, FR-4 (2-layer board), wiring: 50%, wind speed: 0m/s

5. ELECTRICAL CHARACTERISTICS

● DC Characteristics

(Unless otherwise specified: Ta=25°C, Cin=Cout=1μF/Ceramics)

Item	Symbol	Conditions	Min.	Typ.	Max.	Unit	Measuring circuit
Output voltage	V _{OUT}	V _{DD} =V _{CE} =V _{OUT} (S)+1.0V, I _{OUT} =50mA	V _{OUT} (S) ×0.98	—	V _{OUT} (S) ×1.02	V	Fig.1
Output current	I _{OUT}	V _{DD} =V _{CE} =V _{OUT} (S)+1.0V	150	—	—	mA	Fig.1
Input voltage	V _{DD}	—	—	—	5.5	V	Fig.1
Input stability	$\frac{dV_{OUT}}{dV_{DD} \cdot V_{OUT}}$	V _{OUT} (S)+0.5V≤V _{DD} ≤5.5V, V _{CE} =V _{DD} I _{OUT} =50mA	—	0.05	0.2	%/V	Fig.2
Input-output potential difference	V _{diff}	V _{diff} =V _{DDA} -V _{OUT} (S),*) V _{DDA} : V _{DD} value with V _{OUT} set to 98%	3.2V<V _{OUT} (S)<=4.0V	—	0.25	0.35	V
			2.6V<V _{OUT} (S)<=3.2V	—	0.30	0.45	V
			2.0V<V _{OUT} (S)<=2.6V	—	0.40	0.55	V
			1.5V<=V _{OUT} (S)<=2.0V	—	0.50	0.65	V
Load stability	$\frac{dV_{OUT}}{dI_{OUT}}$	V _{DD} =V _{CE} =V _{OUT} (S)+1.0V 1mA≤I _{OUT} ≤150mA	—	20	40	mV	Fig.1
Current consumption (no-load operation)	I _{SS1}	V _{DD} =V _{CE} =V _{OUT} (S)+1.0V, I _{OUT} =0mA	—	30	50	μA	Fig.3.1
Current consumption (standby)	I _{SS0}	V _{DD} =V _{OUT} (S)+1.0V, V _{CE} =V _{SS}	—	0.01	1	μA	Fig.3.2
Limited current	I _{LIM}	V _{DD} =V _{CE} =V _{OUT} (S)+1.0V	—	350	—	mA	Fig.1
Short-circuit current	I _{SHORT}	V _{DD} =V _{CE} =V _{OUT} (S)+1.0V, V _{OUT} =V _{SS}	—	50	—	mA	Fig.1
Discharge Tr ON resistance	R _{DIST}	V _{DD} =4.0V, V _{CE} =V _{SS} , V _{OUT} =3.0V	66	110	154	Ω	Fig.7
CE HIGH level input voltage	V _{CEH}	V _{DD} =V _{OUT} (S)+1.0V	1.1	—	V _{DD}	V	Fig.6
CE LOW level input voltage	V _{CEL}	V _{DD} =V _{OUT} (S)+1.0V	V _{SS}	—	0.25	V	Fig.6
CE HIGH level input current	I _{CEH}	V _{DD} =V _{OUT} (S)+1.0V, V _{CE} =1.1V	-1.95	-1	-0.45	μA	Fig.6
CE LOW level input current	I _{CEL}	V _{DD} =V _{OUT} (S)+1.0V, V _{CE} =V _{SS}	-0.1	—	0.1	μA	Fig.6

(Unless otherwise specified: Ta=25°C, Cin=COUT=1μF/Ceramics)

Item	Symbol	Conditions	Min.	Typ.	Max.	Unit	Measuring circuit
Output voltage temperature coefficient	$\frac{dV_{OUT}}{dT_a}$	V _{DD} =V _{CE} =V _{OUT} (S)+1.0V -40 ≤T _a ≤85°C, I _{OUT} =50mA	—	±100	—	ppm/	Fig.1
Ripple rejection	RR	V _{DD} =V _{CE} =V _{OUT} (S)+1.0V, I _{OUT} =50mA, f=1kHz, V _{ripple} =0.2Vp-pAC	—	60	—	dB	Fig.4

Note 1) V_{OUT} : Actual output voltage valueV_{OUT}(S): Rated output voltage value

5. ELECTRICAL CHARACTERISTICS

■ Electrical characteristics [DC Characteristics]

1. Output voltage (Measuring circuit, Fig.1)

Range of output value when the input voltage is changed in the specified output current and temperature.

V_{OUT}: Actual output voltage value

V_{OUT(S)}: Rated output voltage value $V_{OUT(S)} \cdot 0.98 \leq V_{OUT} \leq V_{OUT(S)} \cdot 1.02$

The output voltage accuracy guarantees +/-2[%].

<Conditions>

Supply output current I_{OUT}=50 [mA], and change the input voltage from V_{OUT(S)}+0.1 [V] to 5.5 [V].

2. Output current (Measuring circuit, Fig.1)

Current that is stably output with normal operation.

Minimum current value when the actual output voltage V_{OUT} become less than 95% of the rated output value V_{OUT(S)} by increasing the output current by degrees.

<Conditions>

Apply the input voltage of V_{OUT(S)}+1.0 [V].

3. Input stability (Measuring circuit, Fig.2)

Maximum value in change of the output voltage that is caused when changing the input voltage while maintaining the output current.

• V_{OUT1}: Changed output voltage

• V_{IN}: Changed input voltage (Rated output voltage +0.5 [V] ≤ V_{IN} ≤ Maximum input voltage)

• V_{OUT}: Rated output voltage

Rated output voltage

$$\text{Input Stability} = \frac{\Delta V_{OUT1}}{\Delta V_{IN} \cdot V_{OUT}}$$

<Conditions>

Supply output current I_{OUT}=50 [mA], and apply the input voltage from V_{OUT(S)}+0.5 [V] to rated input voltage 5.5 [V].

4. Load stability (Measuring circuit, Fig.1)

Maximum value in change of the output voltage that is caused when changing the output current while maintaining the input voltage.

<Conditions>

Maximum value in change of the output voltage that is caused when changing the output current from 1 [mA] to 150 [mA] while maintaining the input voltage V_{OUT(S)}+1.0 [V].

5. Input-output potential difference (Measuring circuit, Fig.2)

Potential difference between input and output voltages when changing the output current as a parameter.

Potential difference between input and output voltages when the output voltage lowers to 98 [%] by reducing the input voltage by degrees while maintaining the output current.

<Conditions>

Specify input-output potential differences Typ. and Max., using output current I_{OUT}=150 [mA] as the reference.

6. Output voltage temperature coefficient (Measuring circuit, Fig.1)

Rate in change of the output voltage that is caused when changing the ambient temperature while maintaining the output current. Obtained from the following formula.

$$\text{Output voltage temperature coefficient [ppm/ } ^\circ\text{C]} = \frac{\Delta V_{OUT}}{\Delta T_a \cdot V_{OUT}} [\text{ppm/ } ^\circ\text{C}] = \frac{\Delta V_{OUT}}{\Delta T_a} [\text{mV/ } ^\circ\text{C}] \cdot \frac{1}{V_{OUT(S)}} [\text{V}] \cdot 1000$$

<Conditions>

Rate in change of the output voltage that is caused when changing the rated range from -40 [°C] to +85 [°C] while setting the input voltage to $V_{OUT}(S)+1.0$ [V] and applying the output current $I_{OUT}=50$ [mA].

7. Current consumption (no-load operation) (Measuring circuit, Fig.3.1)

CE pin= V_{DD} (IC active state), operating current at a specific input voltage and load current.

<Conditions>

Current value at CE= V_{DD} and $I_{OUT}=0$ [mA]; the input voltage is set to $V_{OUT}(S)+1.0$ [V].

8. Current consumption (standby) (Measuring circuit, Fig.3.2)

Input current value that is obtained when changing the input voltage while setting CE pin= V_{SS} and output open (no connection) state.

<Conditions>

Current value at CE= V_{SS} and $I_{OUT}=0$ [mA]; the input voltage is set to $V_{OUT}(S)+1.0$ [V].

9. Limited current (Measuring circuit, Fig.1)

Output current value required to run the overcurrent protection circuit.

Maximum current value when the output voltage drastically lowers by the overcurrent protection circuit that prevents overcurrent. (Max. IC output current)

<Conditions>

Set the input voltage to $V_{OUT}(S)+1.0$ [V] and the CE pin voltage to V_{DD} .

10. Short-circuit current (Measuring circuit, Fig.1)

Value of the current that is supplied to the output when the output pin is short-circuited with V_{SS} . Output current value required to run the short-circuit current protection circuit.

<Conditions>

Set the input voltage to $V_{OUT}(S)+1.0$ [V] and the CE pin voltage to V_{DD} , then connect the output pin to V_{SS} .

11. Ripple rejection (Measuring circuit, Fig.4)

Indicates the ratio with which AC components included in the input voltage appear in the output voltage, by [dB].

<Conditions>

Input voltage=CE pin voltage= $V_{OUT}(S)+1.0$ [V] Output current $I_{OUT}=50$ [mA]

Frequency obtained by superposing the sine wave of 0.2 [Vp-pAC] with the input voltage: 10 [Hz] to 100 [kHz]

12. Discharge Tr ON resistance (Measuring circuit, Fig.7)

ON resistance value of internal transistor that removes (discharges) the C_{out} charge in the standby state.

<Conditions>

Obtained from the value of the current that is supplied to the V_{OUT} pin when the power is applied externally at input voltage=4.0V, CE= V_{SS} , $V_{OUT}=3V$.

■ Electrical characteristics [AC Characteristics]

13. Input transient response (Measuring circuit, Fig.2)

Change of the output voltage that is caused when the input voltage is changed instantaneously.

<Conditions>

Response of the output voltage that is caused when the input voltage is changed from $V_{OUT}+1.0$ [V] to $V_{OUT}+2.0$ [V] or from $V_{OUT}+2.0$ [V] to $V_{OUT}+1.0$ [V] at 5[μs]. Output current $I_{OUT}=50$ [mA]

5. ELECTRICAL CHARACTERISTICS

14. Load transient response

(Measuring circuit, Fig.1)

Change of the output voltage that is caused when the output current is changed at 500 [ns].

<Conditions>

- 1) Response of the output voltage that is caused when the output current is changed from 1.0 [mA] to 50 [mA] or from 50 [mA] to 1.0 [mA]. Input voltage= $V_{OUT}(S)+1.0$ [V], $C_{out}=4.7$ [μ F]
- 2) Response of the output voltage that is caused when the output current is changed from 1.0 [mA] to 150 [mA] or from 150 [mA] to 1.0 [mA]. Input voltage= $V_{OUT}(S)+1.0$ [V], $C_{out}=4.7$ [μ F]

15. CE pin transient response

(Measuring circuit, Fig.5)

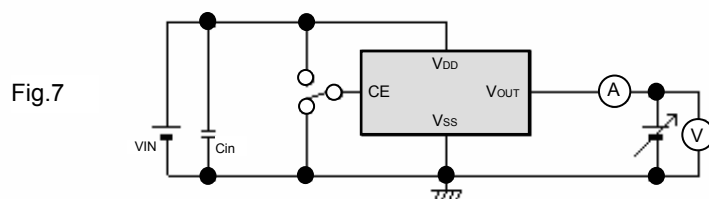
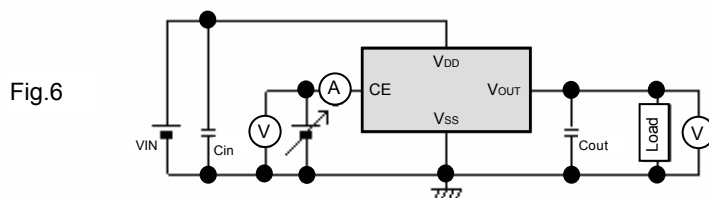
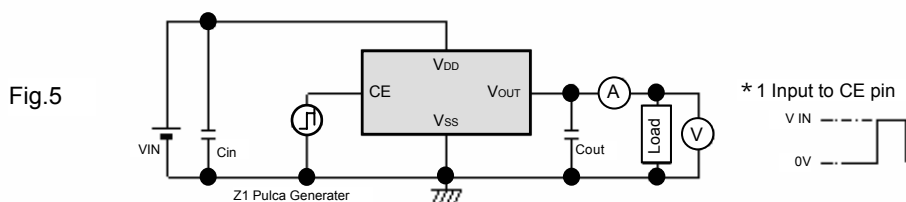
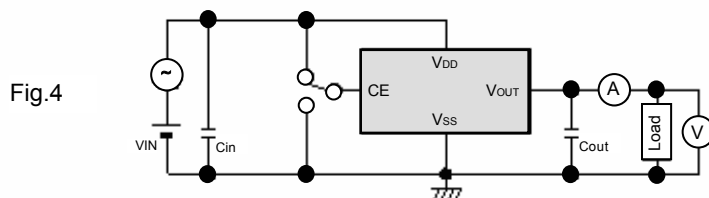
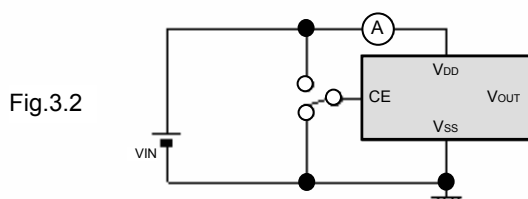
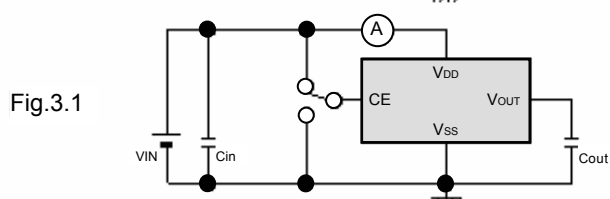
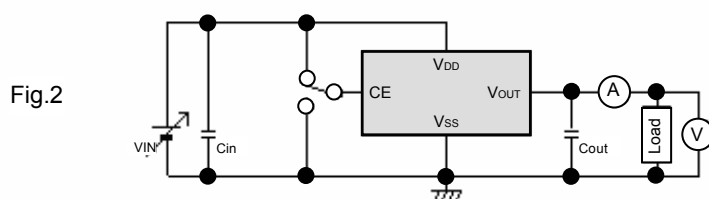
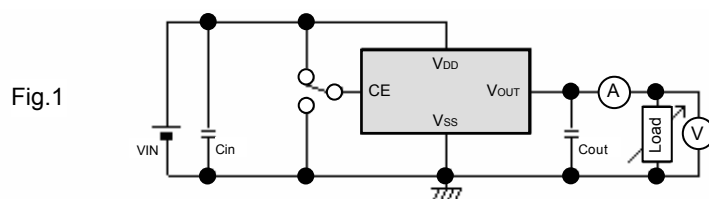
Change of the output voltage that is caused when the CE pin is changed from OFF to ON or from ON to OFF.

<Conditions>

Output current $I_{OUT}=50$ [mA], input voltage= $V_{OUT}(S)+1.0$ [V]

Change of the output voltage that is caused when the CE pin voltage is changed from 0 [V] to more than HIGH level voltage (1.1 [V]) at 1 [μ s].

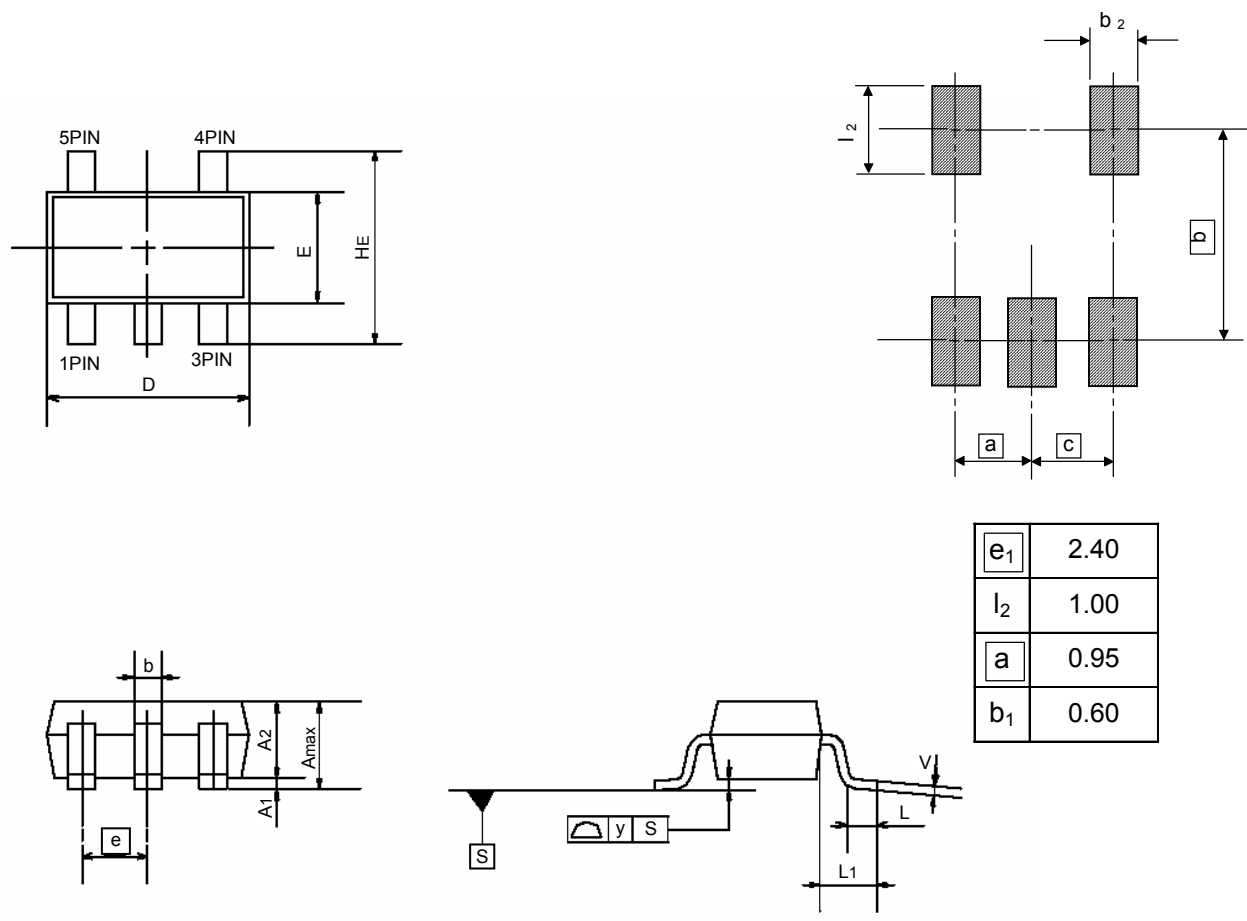
6. MEASURING CIRCUIT



7. DIMENSIONS

7. DIMENSIONS

- SOT23-5

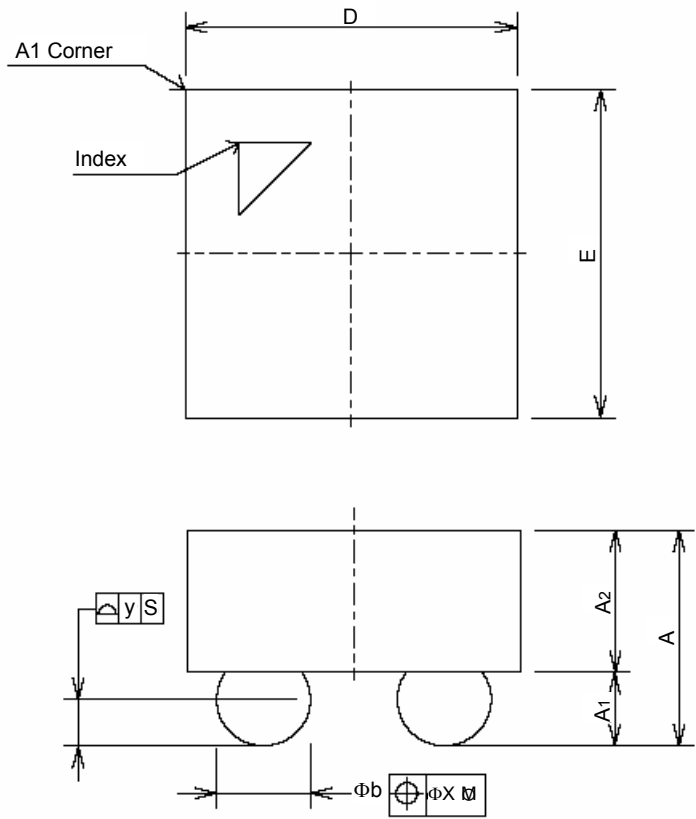


symbol	Dimension in Millimeters		
	Min.	Nom.	Max.
D	—	2.9	—
E	—	1.6	—
A _{MAX}	—	—	1.40
A _L	0	—	0.15
A _e	—	1.1	—
e	—	0.95	—
b	0.3	—	0.5
C	0.1	—	0.26
L	0.2	—	0.6
L1	—	0.6	—
H _E	—	2.8	—
Y	—	—	0.1

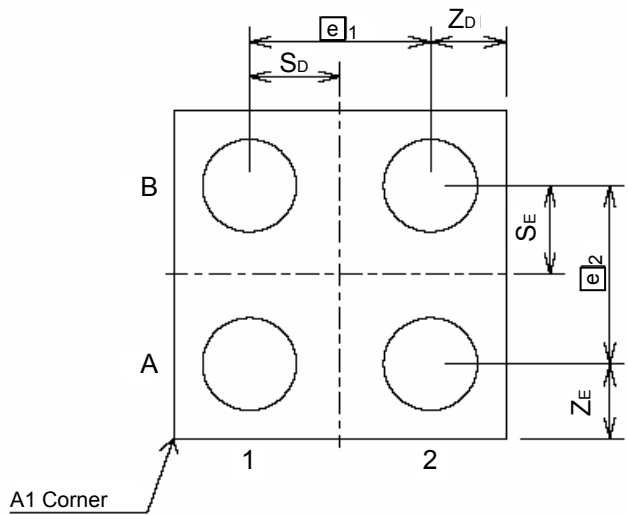
1=1mm

• WCSP-4

Top View



Bottom View



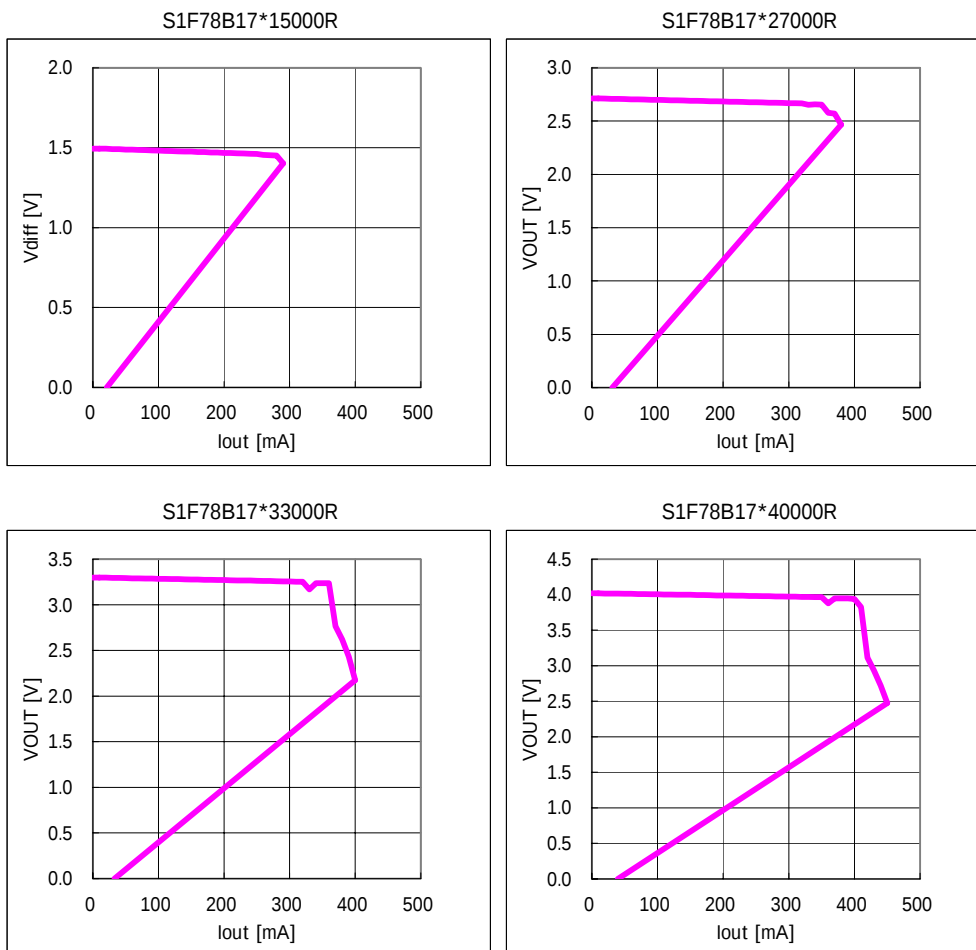
symbol	Dimension in Millimeters		
	Min.	Nom.	Max.
D	—	0.920	—
E	—	0.920	—
A	—	—	0.65
A ₁	—	0.21	—
A ₂	—	—	—
e ₁	—	0.50	—
e ₂	—	0.50	—
b	0.23	0.26	0.29
x	—	—	0.08
y	—	—	0.05
S _D	—	0.25	—
S _E	—	0.25	—
Z _D	—	0.210	—
Z _E	—	0.210	—

8. CHARACTERISTIC EXAMPLES

8. CHARACTERISTIC EXAMPLES

- 1) Characteristics examples between output voltage and output current

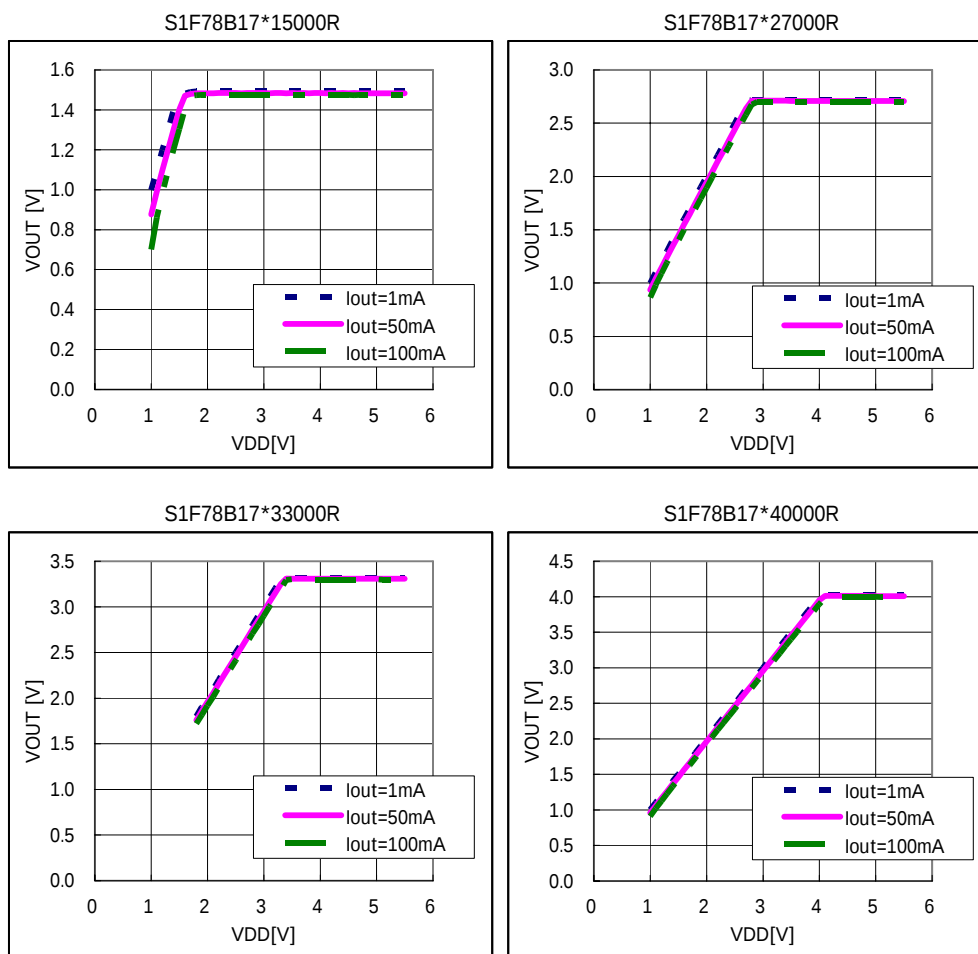
[Measuring conditions] $V_{DD}=V_{OUT}(S)+1.0V$, $V_{SS}=0.0V$, $C_E=V_{DD}$, $T_{opr}=25^{\circ}C$, $C_{in}=C_{out}=1.0\mu F$



8. CHARACTERISTIC EXAMPLES

2) Characteristics examples between output voltage and input voltage

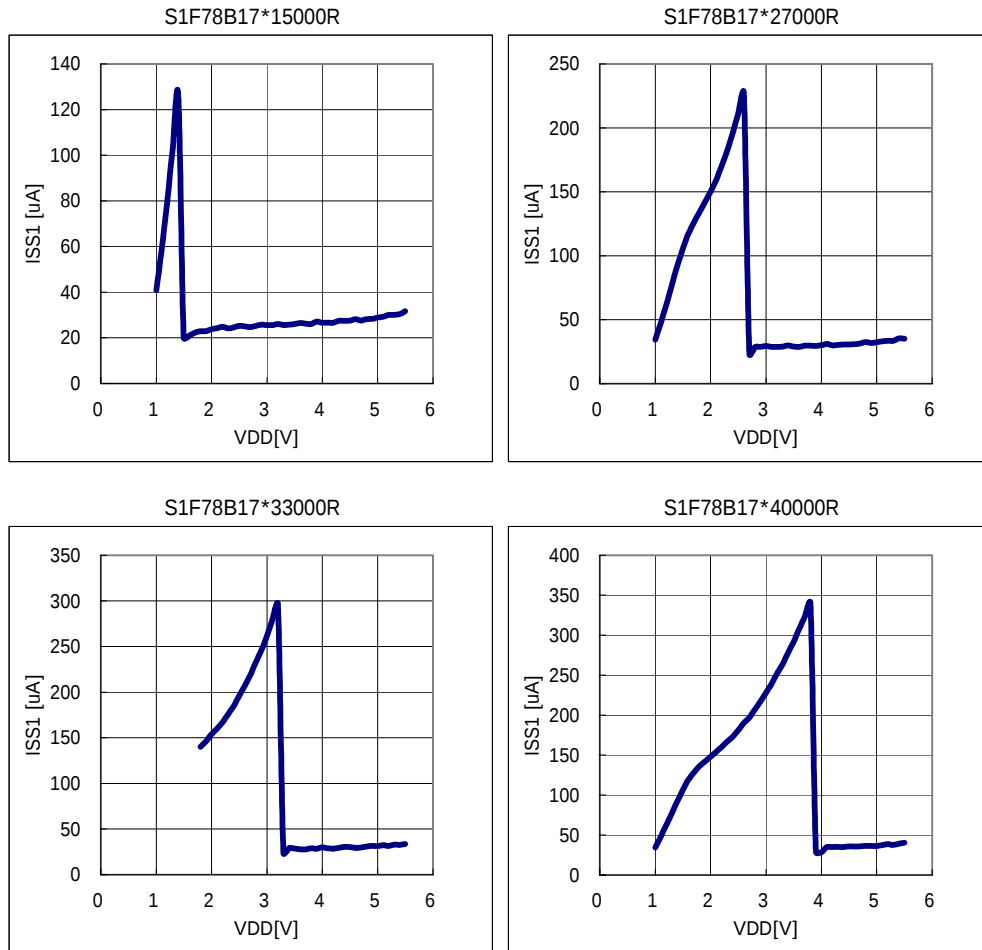
[Measuring conditions] $V_{SS}=0.0V$, $C_E=V_{DD}$, $T_{opr}=25^{\circ}C$, $C_{in}=C_{out}=1.0\mu F$



8. CHARACTERISTIC EXAMPLES

3) Characteristics between consumption current and input voltage

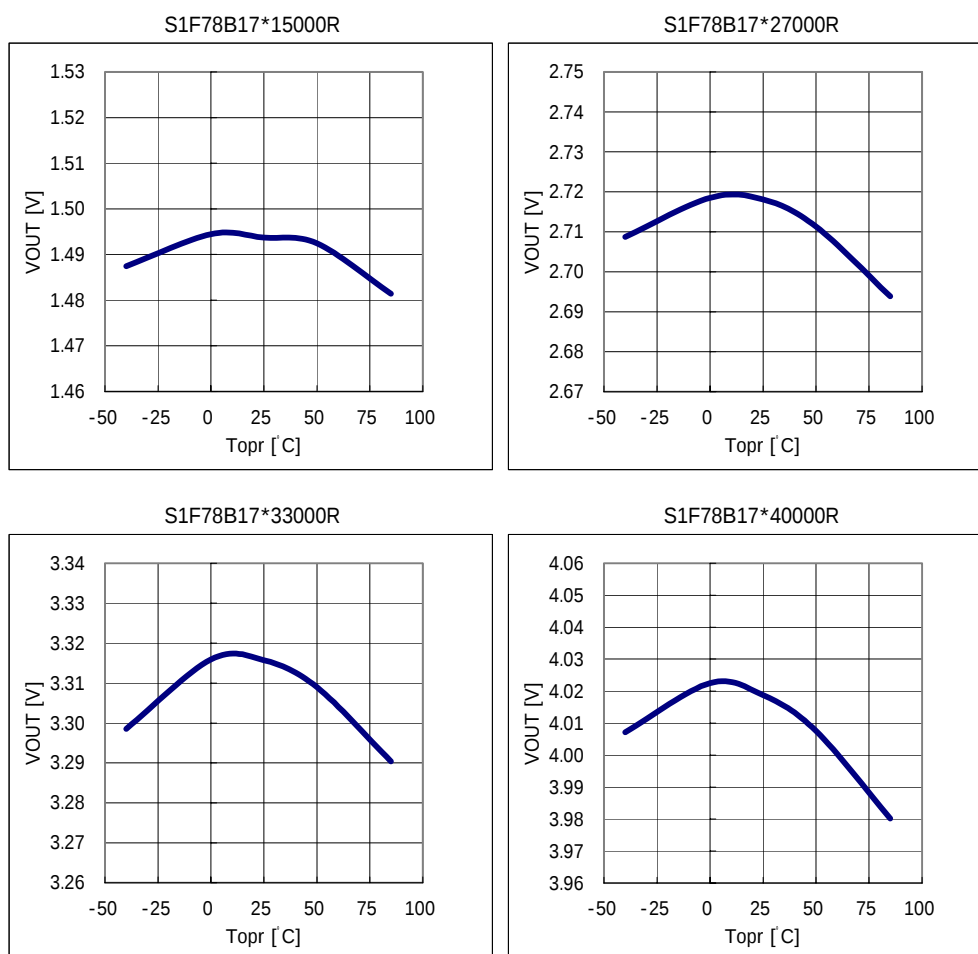
[Measuring conditions] $V_{SS}=0.0V$, $C_E=V_{DD}$, $T_{opr}=25^{\circ}C$, $C_{in}=C_{out}=1.0\mu F$, $I_{out}=0mA$



8. CHARACTERISTIC EXAMPLES

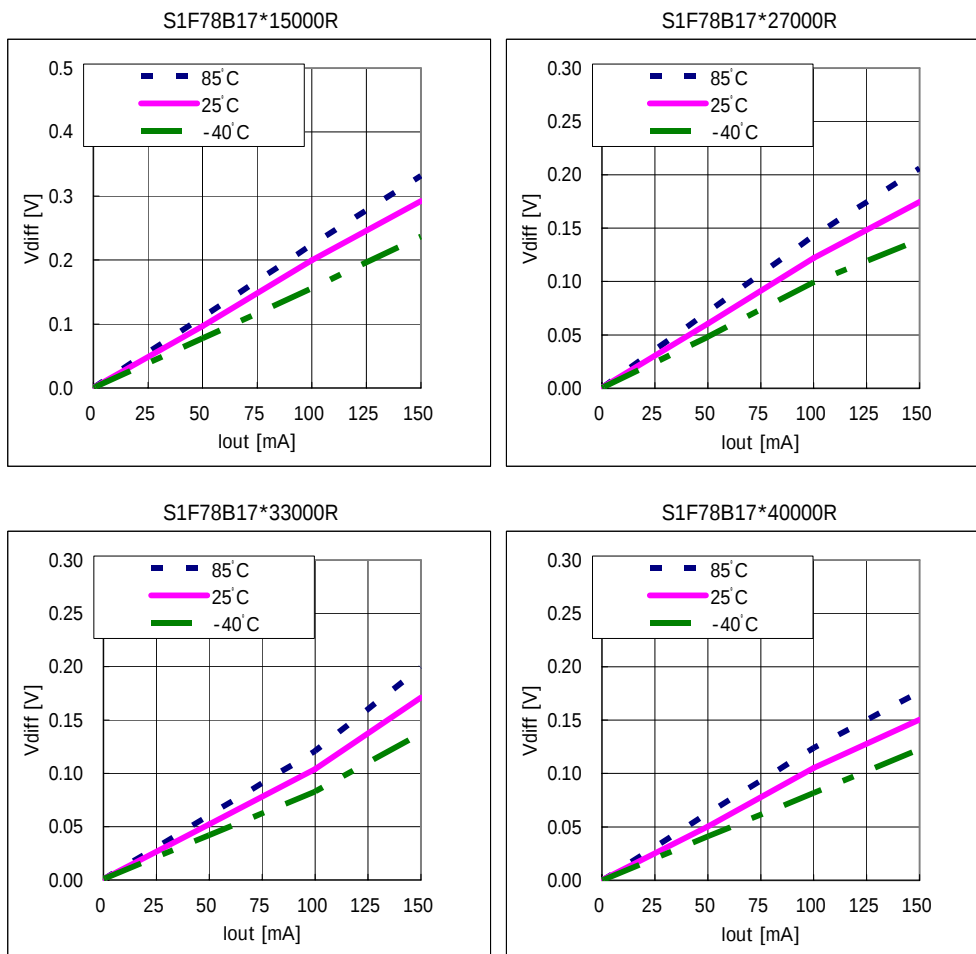
4) Characteristics between output voltage and ambient temperature

[Measuring conditions] $V_{DD}=V_{OUT}(S)+1.0V$, $V_{SS}=0.0V$, $C_E=V_{DD}$, $C_{in}=C_{out}=1.0\mu F$, $I_{out}=0mA$

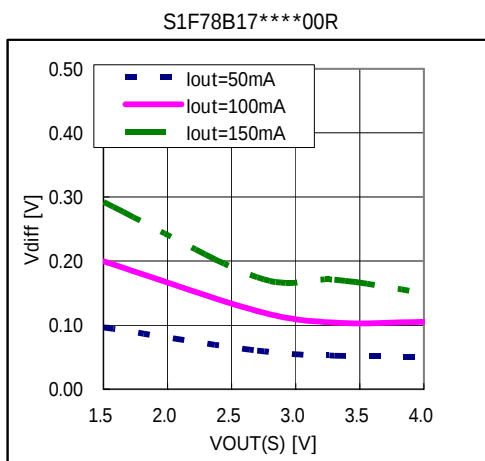


8. CHARACTERISTIC EXAMPLES

5) Characteristic examples between input-output potential difference and output current

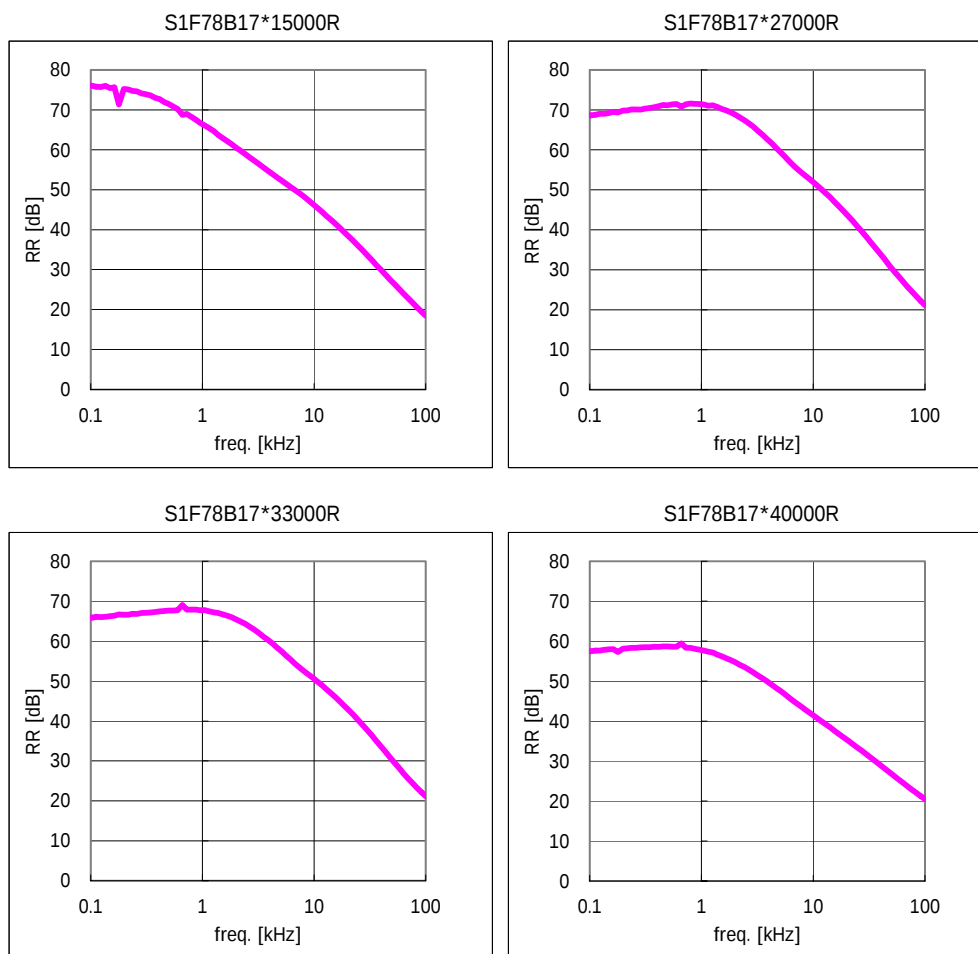


6) Characteristic examples between input-output potential difference and set output voltage



7) Characteristics between ripple rejection and frequency

[Measuring conditions] $V_{DD}=V_{OUT}(S)+1.0V+0.2V_{p-p}$, $V_{SS}=0.0V$, $CE=V_{DD}$, $T_{opr}=25$, $C_{in}=C_{out}=1.0\mu F$,
 $I_{out}=50mA$



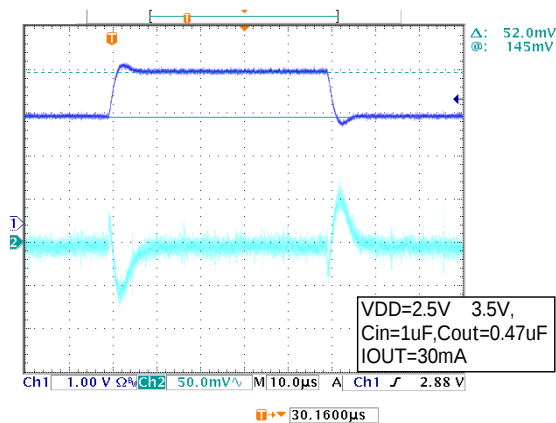
8. CHARACTERISTIC EXAMPLES

8) Characteristics examples of input transient response

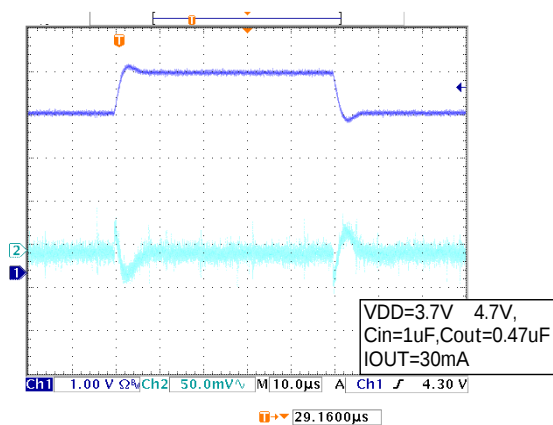
[Measuring conditions] $V_{SS}=0.0V$, $CE=V_{DD}$, $T_{opr}=25^{\circ}C$

* Upper: V_{DD} , Lower: V_{OUT} in the following waveforms.

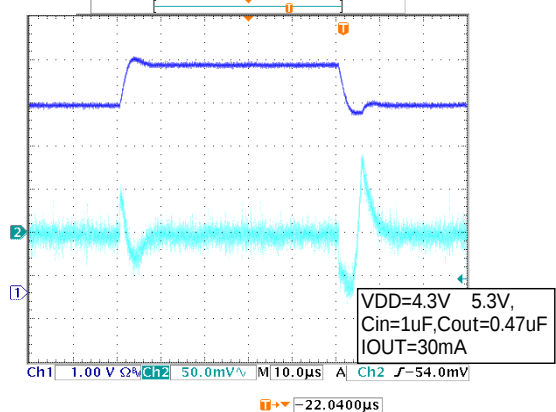
• S1F78B17*15000R



• S1F78B17*27000R



• S1F78B17*33000R

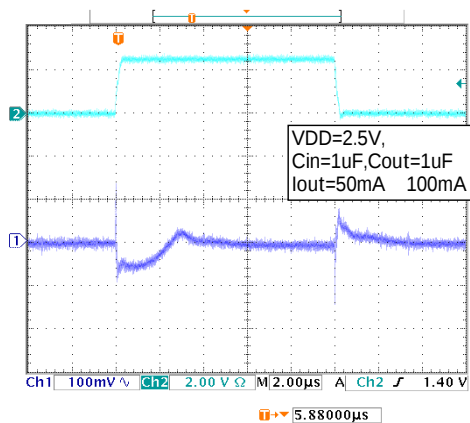
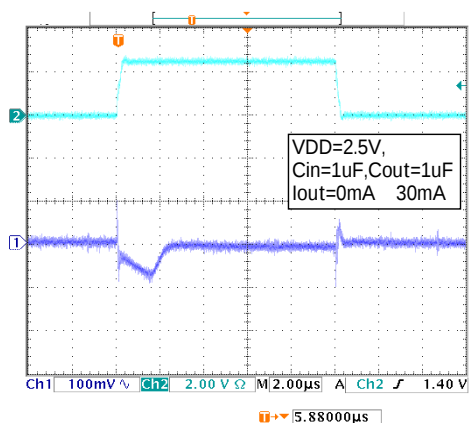


9) Characteristics examples of load transient response

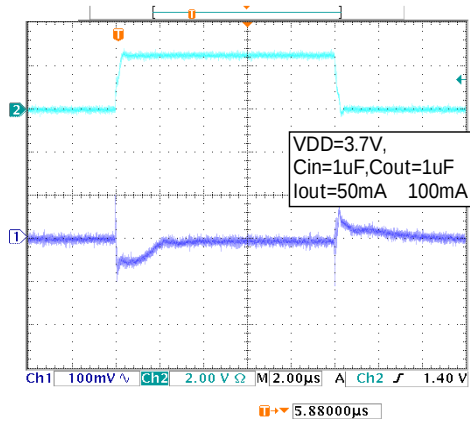
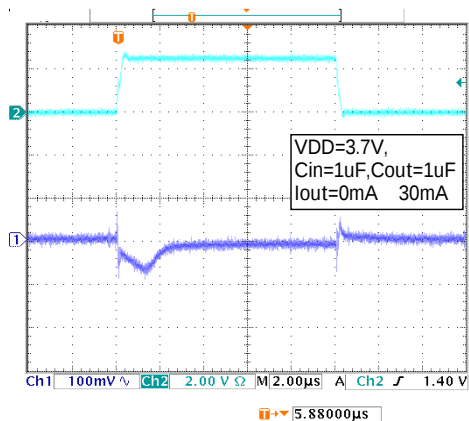
[Measuring conditions] $V_{SS}=0.0V$, $CE=V_{DD}$, $T_{opr}=25^{\circ}C$

* Upper: V_{DD} , Lower: V_{OUT} in the following waveforms.

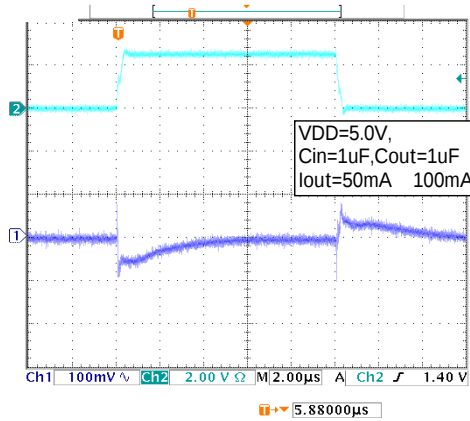
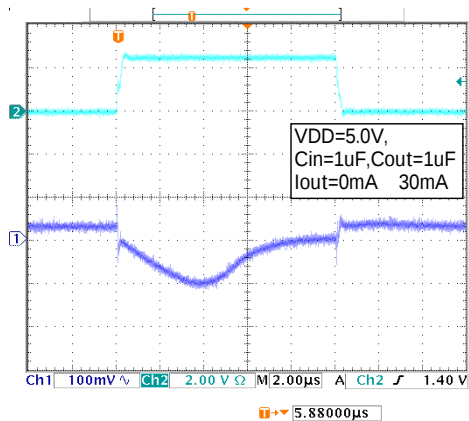
• S1F78B17*15000R



• S1F78B17*27000R



• S1F78B17*40000R



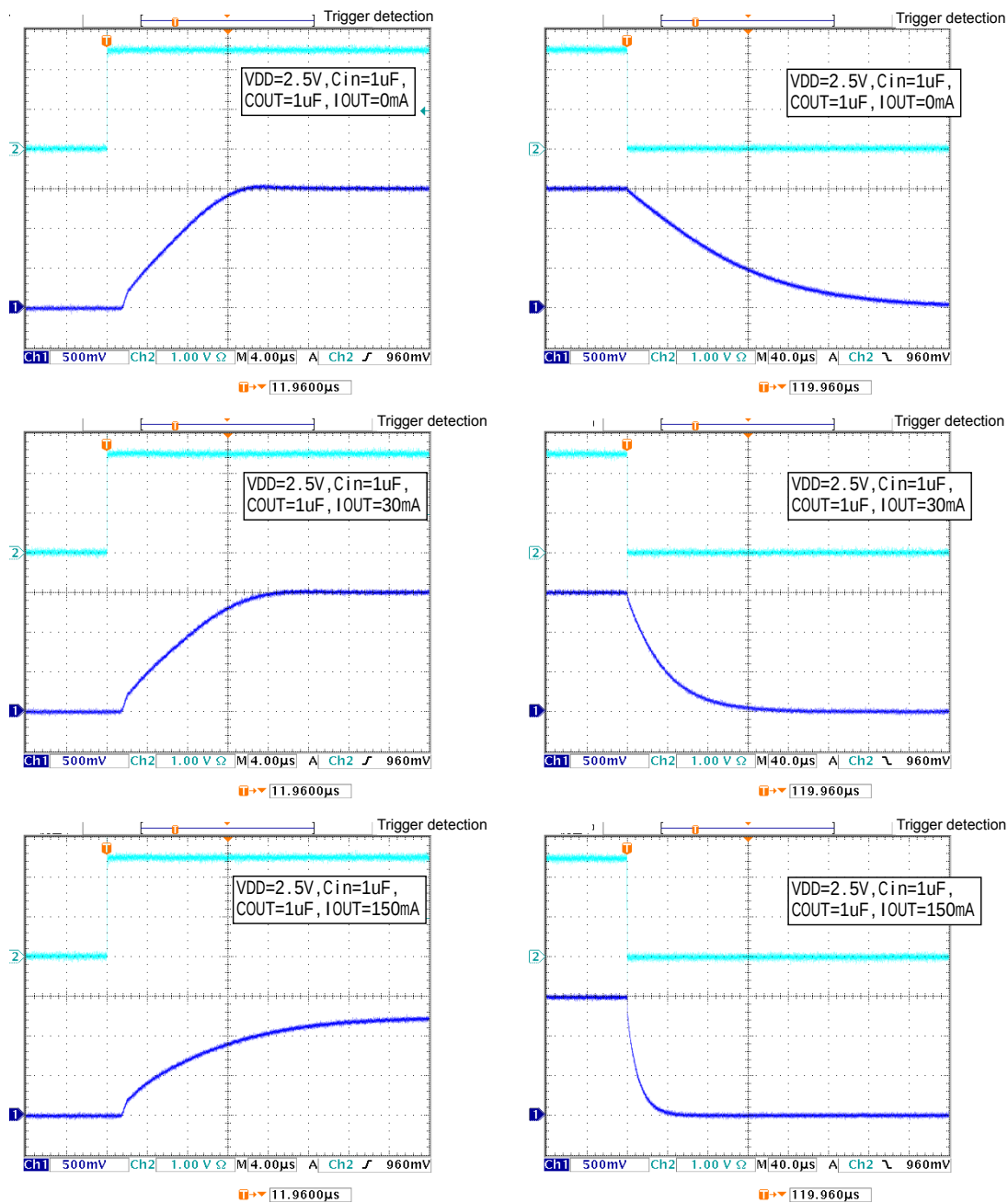
8. CHARACTERISTIC EXAMPLES

10) Characteristics examples of CE pin transient response

[Measuring conditions] $V_{SS}=0.0V$, $CE=V_{SS}$ V_{DD} , $T_{opr}=25^{\circ}C$

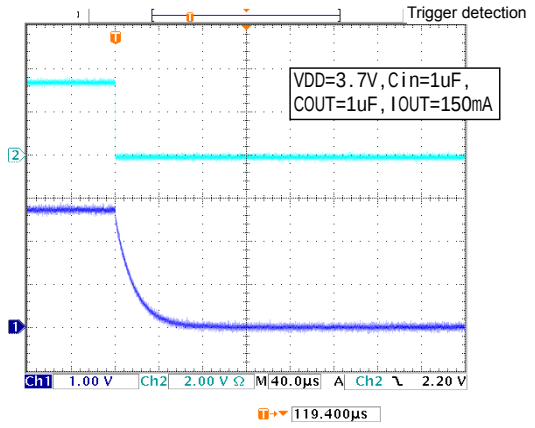
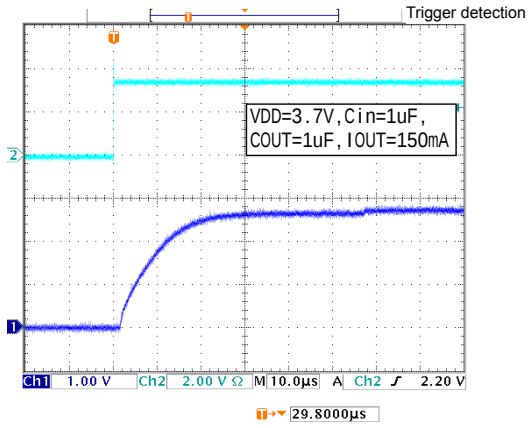
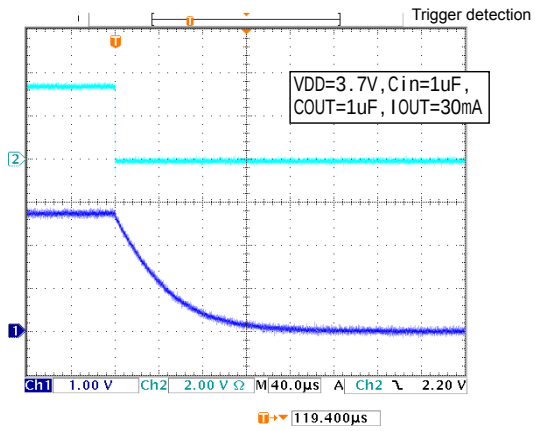
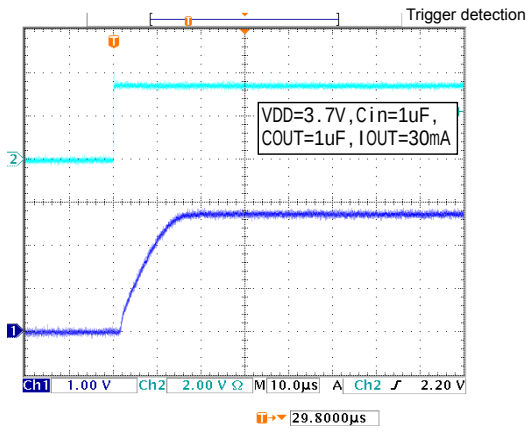
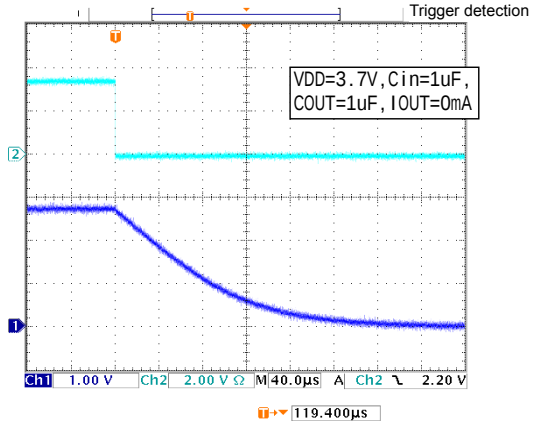
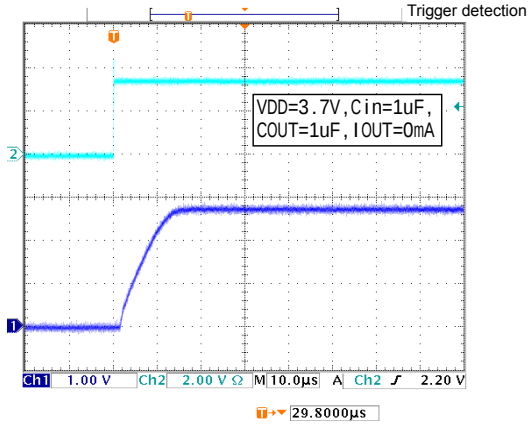
* Upper: CE, Lower: V_{OUT} in the following waveforms.

● S1F78B17*15000R



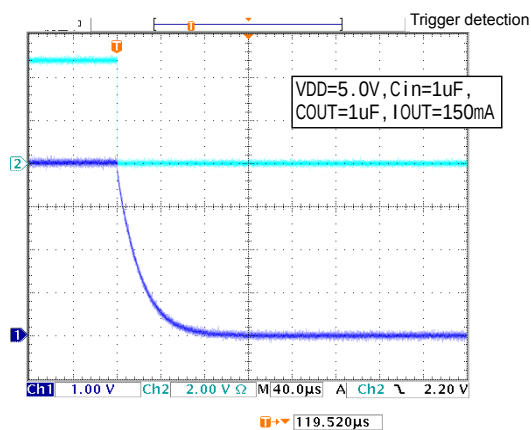
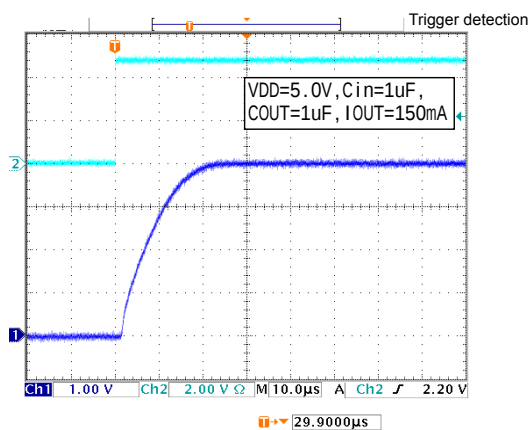
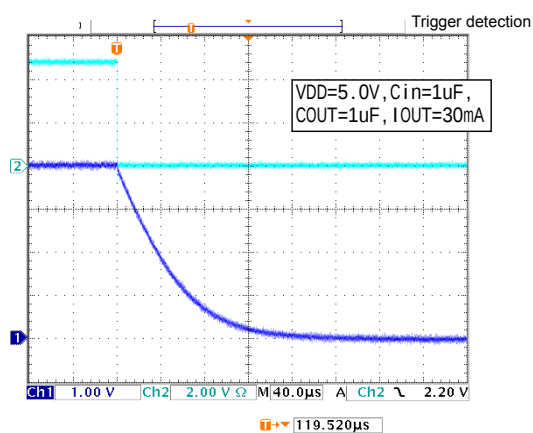
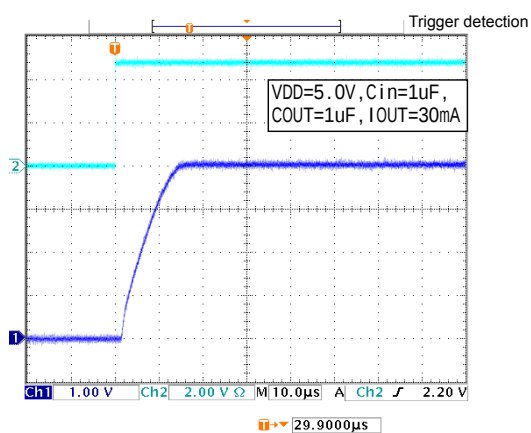
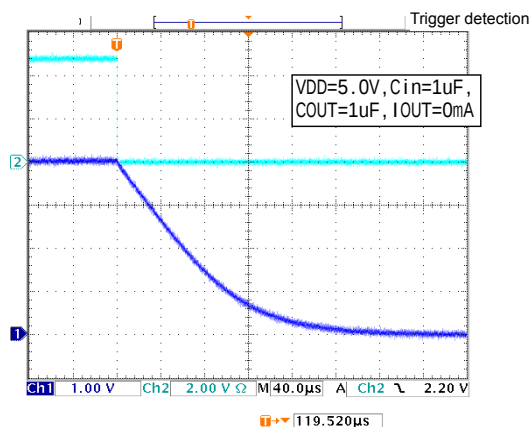
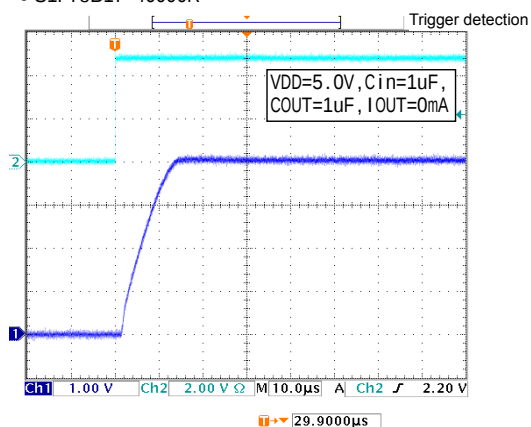
8. CHARACTERISTIC EXAMPLES

● S1F78B17*27000R



9. PRECAUTIONS ON EXTERNAL PARTS

● S1F78B17*40000R



9. PRECAUTIONS ON EXTERNAL PARTS

- Always add an input capacitor (C_{in}) and output capacitor (C_{out}) to stabilize this IC.
- For VDD and VSS circuit, provide enough noise suppression on the board.
- Keep the distance from this IC to C_{in} and C_{out} as short as possible.

AMERICA

EPSON ELECTRONICS AMERICA, INC.**HEADQUARTERS**

2580 Orchard Parkway
San Jose, CA 95131, USA
Phone: +1-800-228-3964 FAX: +1-408-922-0238

SALES OFFICES**Northeast**

301 Edgewater Place, Suite 210
Wakefield, MA 01880, U.S.A.
Phone: +1-800-922-7667 FAX: +1-781-246-5443

EUROPE

EPSON EUROPE ELECTRONICS GmbH**HEADQUARTERS**

Riesstrasse 15
80992 Munich, GERMANY
Phone: +49-89-14005-0 FAX: +49-89-14005-110

ASIA

EPSON (CHINA) CO., LTD.

23F, Beijing Silver Tower 2# North RD DongSanHuan
ChaoYang District, Beijing, CHINA
Phone: +86-10-6410-6655 FAX: +86-10-6410-7320

SHANGHAI BRANCH

7F, High-Tech Bldg., 900, Yishan Road,
Shanghai 200233, CHINA
Phone: +86-21-5423-5522 FAX: +86-21-5423-5512

EPSON HONG KONG LTD.

20/F., Harbour Centre, 25 Harbour Road
Wanchai, Hong Kong
Phone: +852-2585-4600 FAX: +852-2827-4346
Telex: 65542 EPSCO HX

EPSON Electronic Technology Development (Shenzhen) LTD.

12/F, Dawning Mansion, Keji South 12th Road,
Hi-Tech Park, Shenzhen
Phone: +86-755-2699-3828 FAX: +86-755-2699-3838

EPSON TAIWAN TECHNOLOGY & TRADING LTD.

14F, No. 7, Song Ren Road,
Taipei 110
Phone: +886-2-8786-6688 FAX: +886-2-8786-6660

EPSON SINGAPORE PTE., LTD.

1 HarbourFront Place,
#03-02 HarbourFront Tower One, Singapore 098633
Phone: +65-6586-5500 FAX: +65-6271-3182

SEIKO EPSON CORPORATION**KOREA OFFICE**

50F, KLI 63 Bldg., 60 Yoido-dong
Yongdeungpo-Ku, Seoul, 150-763, KOREA
Phone: +82-2-784-6027 FAX: +82-2-767-3677

GUMI OFFICE

2F, Grand B/D, 457-4 Songjeong-dong,
Gumi-City, KOREA
Phone: +82-54-454-6027 FAX: +82-54-454-6093

SEIKO EPSON CORPORATION**SEMICONDUCTOR OPERATIONS DIVISION****IC Sales Dept.****IC International Sales Group**

421-8, Hino, Hino-shi, Tokyo 191-8501, JAPAN
Phone: +81-42-587-5814 FAX: +81-42-587-5117

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